

## Features

- Excellent package for good heat dissipation
- Ultra low gate charge
- Low reverse transfer capacitance
- Fast switching capability
- Avalanche energy specified

## Product Summary

$V_{DS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
60V	50mΩ@10V	8A
	60mΩ@4.5V	

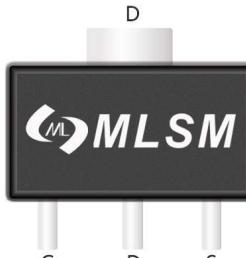
## Application

- Power switching application

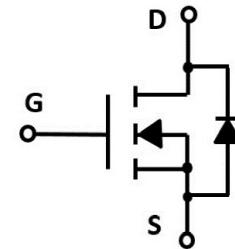


0G08A: Device code  
XXXX: Code

Marking and pin assignment



SOT-89-3L top view



Schematic diagram



Halogen-Free

## Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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## Common Ratings (TC=25°C Unless Otherwise Noted)

$V_{DS}$	Drain-Source Breakdown Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$T_J$	Maximum Junction Temperature	150	°C
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$I_S$	Diode Continuous Forward Current	8	A

## Mounted on Large Heat Sink

$I_{DM}$	Pulse Drain Current Tested	Tc=25°C	33	A
$I_D$	Continuous Drain Current	Tc=25°C	8	A
$P_D$	Maximum Power Dissipation	Tc=25°C	0.5	W
$R_{θJA}$	Thermal Resistance Junction-Ambient		200	°C/W

## Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MZ0G08A	SOT-89-3L	0G08A	1,000	10,000	40,000	7" reel

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)</b>						
BV <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60	--	--	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	--	--	1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	--	--	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.5	2.5	V
R <sub>DS(on)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =4A	--	38	50	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	--	42	60	mΩ

**Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)**

C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1MHz	--	550	--	pF
C <sub>OSS</sub>	Output Capacitance		--	43	--	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance		--	35	--	pF

**Switching Characteristics**

Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =30V, I <sub>D</sub> =8A, V <sub>GS</sub> =10V	--	11.5	--	nC
Q <sub>gs</sub>	Gate Source Charge		--	1.7	--	nC
Q <sub>gd</sub>	Gate Drain Charge		--	2.5	--	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> =30V, I <sub>D</sub> =8A, V <sub>GS</sub> =10V, R <sub>G</sub> =2.3Ω	--	6	--	nS
t <sub>r</sub>	Turn-on Rise Time		--	11	--	nS
t <sub>d(off)</sub>	Turn-Off Delay Time		--	18	--	nS
t <sub>f</sub>	Turn-Off Fall Time		--	10	--	nS

**Source-Drain Diode Characteristics**

V <sub>SD</sub>	Forward on voltage	T <sub>J</sub> =25°C, I <sub>S</sub> =8A	--	0.8	1.2	V
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### Typical Operating Characteristics

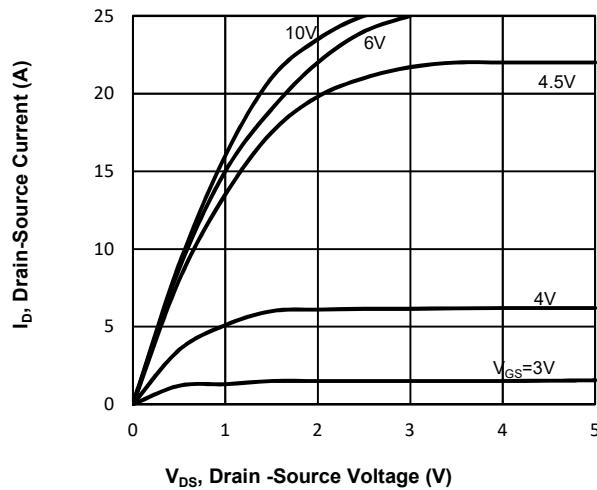


Fig1. Typical Output Characteristics

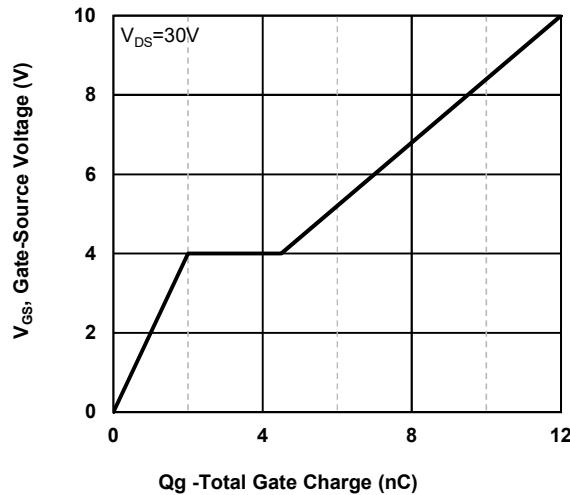


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

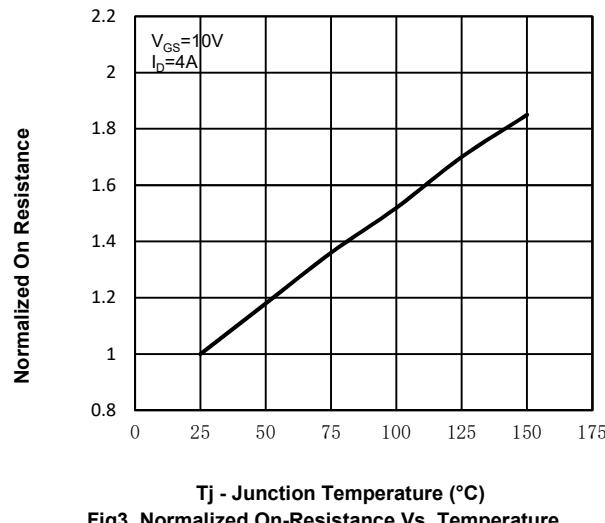


Fig3. Normalized On-Resistance Vs. Temperature

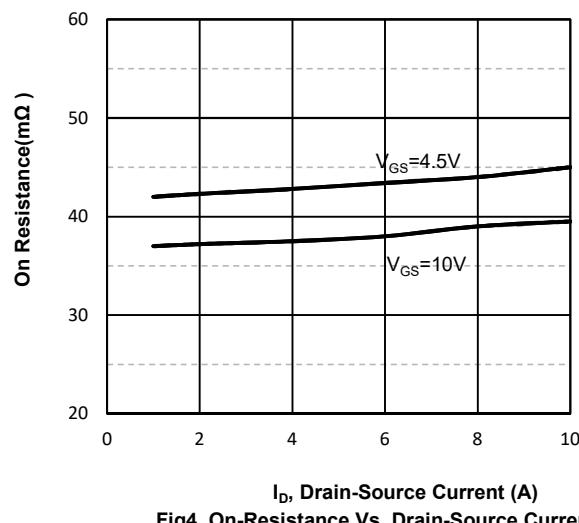


Fig4. On-Resistance Vs. Drain-Source Current

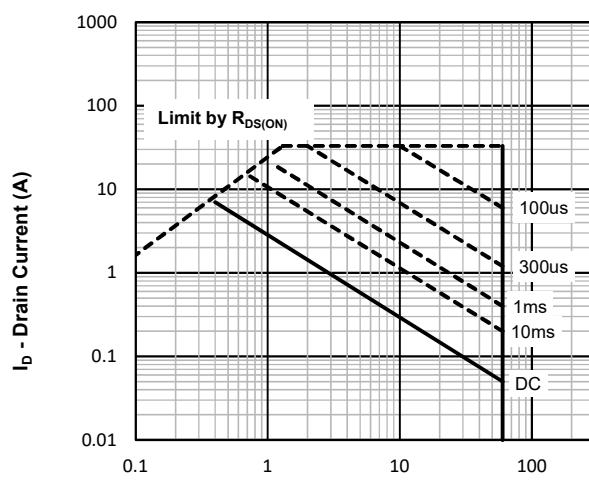


Fig5. Maximum Safe Operating Area

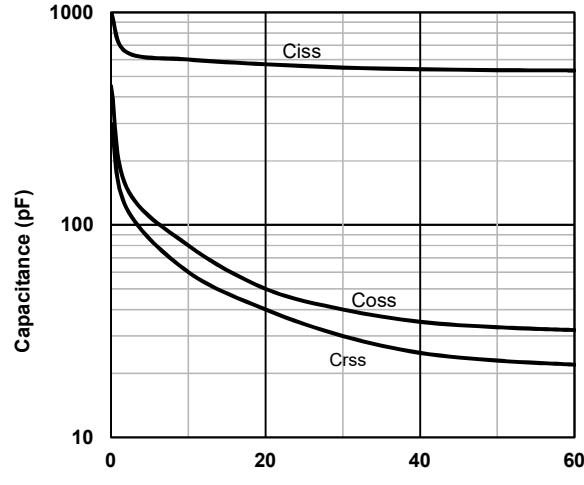
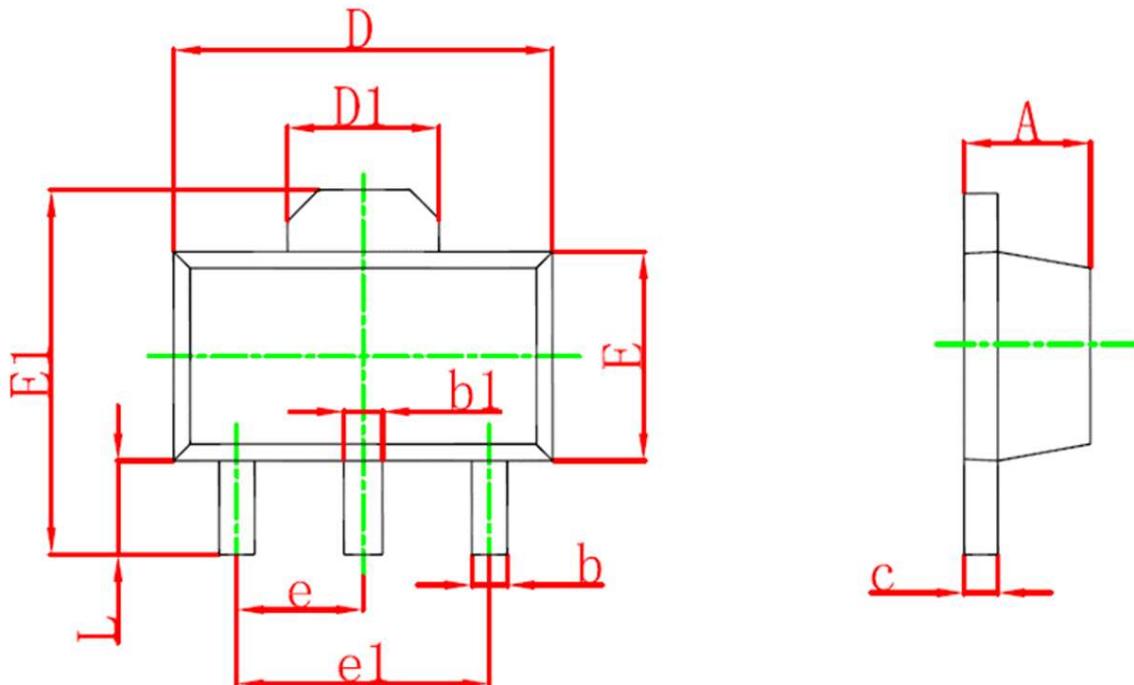


Fig6 Typical Capacitance Vs.Drain-Source Voltage

## SOT-89-3L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions in Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF		0.061 REF	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP		0.060 TYP	
e1	3.000 TYP		0.118 TYP	
L	0.900	1.200	0.035	0.047